GSMBT2222A

NPN EPITAXIAL PLANAR TRANSISTOR

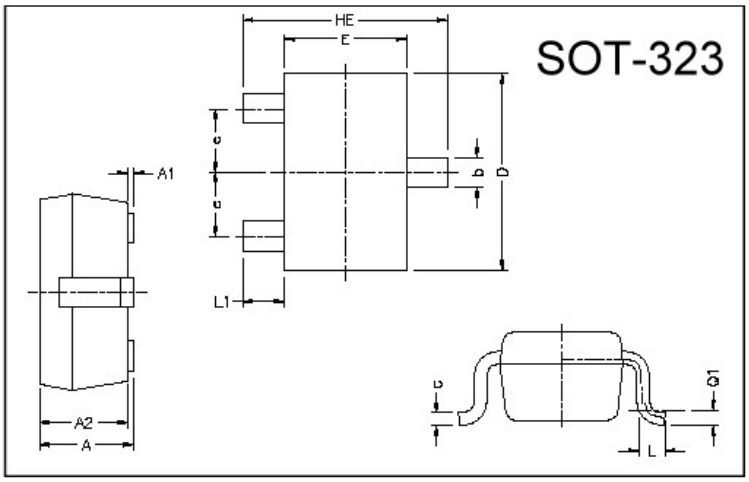
Description

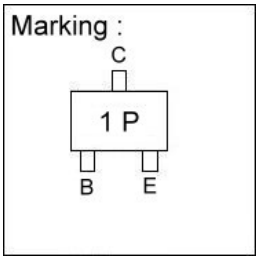
The GSMBT2222A is designed for general purpose amplifier and high speed, medium-power switching applications.

Features

- High frequency current gain
- High speed switching
- For complementary use with PNP type GSMBT2907A

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.80	1.10	L1	0.42 REF.	
A1	0	0.10	L	0.15	0.35
A2	0.80	1.00	b	0.25	0.40
D	1.80	2.20	c	0.10	0.25
E	1.15	1.35	e	0.65 REF.	
HE	1.80	2.40	Q1	0.15 BSC.	

Absolute Maximum Ratings at Ta = 25℃

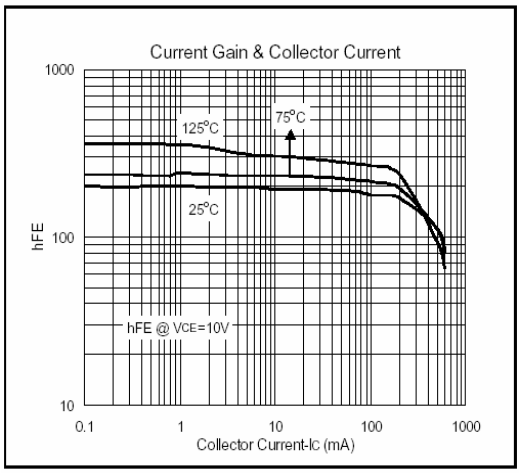
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55 ~ +150	℃
Collector to Base Voltage at Ta=25℃	VCBO	75	V
Collector to Emitter Voltage at Ta=25℃	VCEO	40	V
Emitter to Base Voltage at Ta=25℃	VEBO	6	V
Collector Current at Ta=25℃	IC	600	mA
Total Power Dissipation at Ta=25℃	PD	225	mW

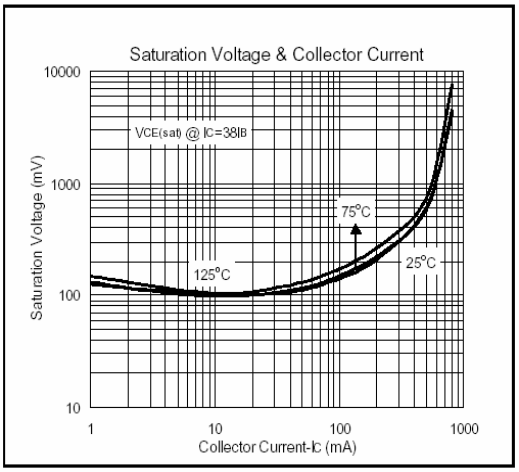
Characteristics at Ta = 25℃

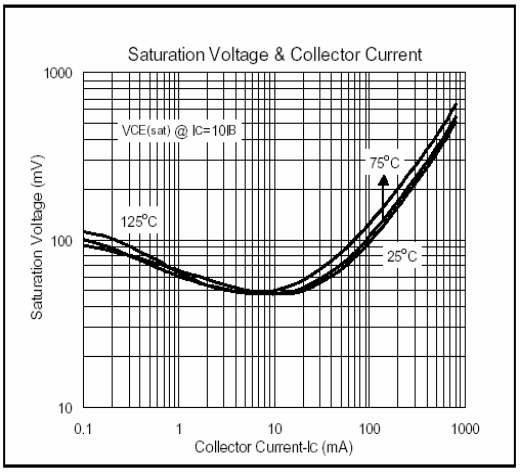
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	75	-	-	V	IC=100uA , IE=0
BVCEO	40	-	-	V	IC=10mA,IB=0
BVEBO	6	-	-	V	IE=10uA ,IC=0
ICBO	-	-	10	nA	VCB=60V, IE=0
ICEX	-	-	10	nA	VCE=60V ,VEB(OFF)=3V
IEBO	-	-	10	nA	VEB=3V
*VCE(sat)1	-	-	500	mV	IC=380mA, IB=10mA
*VCE(sat)2	-	-	1.0	V	IC=500mA, IB=50mA
*VBE(sat)1	-	-	1.2	V	IC=150mA, IB=15mA
*VBE(sat)2	-	-	2.0	V	IC=500mA, IB=50mA
*hFE1	35	-	-		VCE=10V, IC=100uA
*hFE2	50	-	-		VCE=10V, IC=1mA
*hFE3	75	-	-		VCE=10V, IC=10mA
*hFE4	100	-	300		VCE=10V, IC=150mA
*hFE5	40	-	-		VCE=10V, IC=500mA
fT	300	-	-	MHz	VCB=20V, IC=20mA, f=100MHz

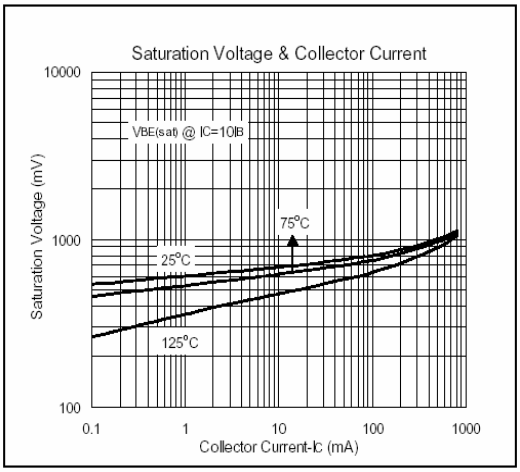
*** Pulse Test: Pulse Width≦380μs, Duty Cycle≦2%**

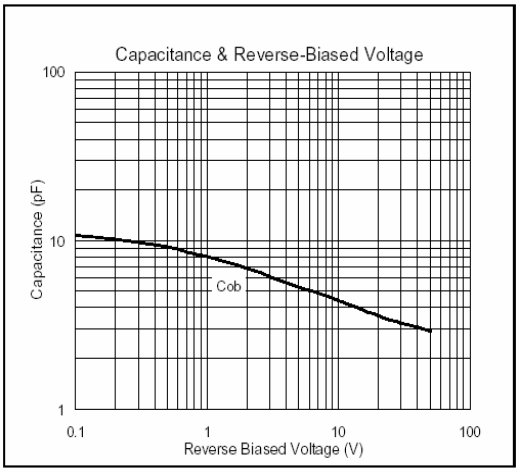
Characteristics Curve

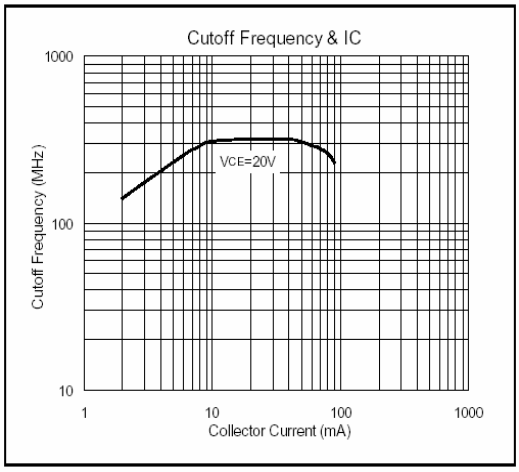












Important Notice:
- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of GTM.
- GTM reserves the right to make changes to its products without notice.
- GTM semiconductor products are not warranted to be suitable for use in life-support Applications, or systems.
- GTM assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

Head Office And Factory:
- **Taiwan**: No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
  TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China**: (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
  TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165